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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

XF

Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	22
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	8K x 8
RAM Size	16К х 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 8x8/10b; D/A 2x8b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	32-WFQFN Exposed Pad
Supplier Device Package	32-HWQFN (5x5)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f104bgana-u0

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Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

○ ROM, RAM capacities

Elash ROM	Data flach	RAM	RL78/G14				
T IdSIT KOW	Data liasii		30 pins	32 pins	36 pins	40 pins	
192 KB	8 KB	20 KB	—	—	—	R5F104EH	
128 KB	8 KB	16 KB	R5F104AG	R5F104BG	R5F104CG	R5F104EG	
96 KB	8 KB	12 KB	R5F104AF	R5F104BF	R5F104CF	R5F104EF	
64 KB	4 KB	5.5 KB Note	R5F104AE	R5F104BE	R5F104CE	R5F104EE	
48 KB	4 KB	5.5 KB Note	R5F104AD	R5F104BD	R5F104CD	R5F104ED	
32 KB	4 KB	4 KB	R5F104AC	R5F104BC	R5F104CC	R5F104EC	
16 KB	4 KB	2.5 KB	R5F104AA	R5F104BA	R5F104CA	R5F104EA	

Elash ROM	Data flach	PAM		RL78	8/G14	
T Idolf TOW	Data liasii		44 pins	48 pins	52 pins	64 pins
512 KB	8 KB	48 KB Note		R5F104GL	—	R5F104LL
384 KB	8 KB	32 KB	_	R5F104GK	—	R5F104LK
256 KB	8 KB	24 KB Note	R5F104FJ	R5F104GJ	R5F104JJ	R5F104LJ
192 KB	8 KB	20 KB	R5F104FH	R5F104GH	R5F104JH	R5F104LH
128 KB	8 KB	16 KB	R5F104FG	R5F104GG	R5F104JG	R5F104LG
96 KB	8 KB	12 KB	R5F104FF	R5F104GF	R5F104JF	R5F104LF
64 KB	4 KB	5.5 KB Note	R5F104FE	R5F104GE	R5F104JE	R5F104LE
48 KB	4 KB	5.5 KB Note	R5F104FD	R5F104GD	R5F104JD	R5F104LD
32 KB	4 KB	4 KB	R5F104FC	R5F104GC	R5F104JC	R5F104LC
16 KB	4 KB	2.5 KB	R5F104FA	R5F104GA	_	

Elash ROM Data flash		DAM	RL78/G14				
T IdSIT KOW	Data hash		80 pins	100 pins			
512 KB	8 KB	48 KB Note	R5F104ML	R5F104PL			
384 KB	8 KB	32 KB	R5F104MK	R5F104PK			
256 KB	8 KB	24 KB Note	R5F104MJ	R5F104PJ			
192 KB	8 KB	20 KB	R5F104MH	R5F104PH			
128 KB	8 KB	16 KB	R5F104MG	R5F104PG			
96 KB	8 KB	12 KB	R5F104MF	R5F104PF			

The flash library uses RAM in self-programming and rewriting of the data flash memory.

The target products and start address of the RAM areas used by the flash library are shown below.

R5F104xD (x = A to C, E to G, J, L): Start address FE900H

R5F104xE (x = A to C, E to G, J, L): Start address FE900H

R5F104xJ (x = F, G, J, L, M, P): Start address F9F00H

R5F104xL (x = G, L, M, P): Start address F3F00H

For the RAM areas used by the flash library, see Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944).



1.5.9 80-pin products





1.6 Outline of Functions

[30-pin, 32-pin, 36-pin, 40-pin products (code flash memory 16 KB to 64 KB)]

Caution This outline describes the functions at the time when Peripheral I/O redirection register 0, 1 (PIOR0, 1) are set to 00H.

					(1/2)			
		30-pin	32-pin	36-pin	40-pin			
	Item	R5F104Ax (x = A, C to E)	R5F104Bx (x = A, C to E)	R5F104Cx (x = A, C to E)	R5F104Ex (x = A, C to E)			
Code flash memo	ry (KB)	16 to 64	16 to 64	16 to 64	16 to 64			
Data flash memor	у (КВ)	4	4	4	4			
RAM (KB)		2.5 to 5.5 Note	2.5 to 5.5 Note	2.5 to 5.5 Note	2.5 to 5.5 Note			
Address space		1 MB						
Main system clock	High-speed system clock High-speed on-chip oscillator clock (fiH)	X1 (crystal/ceramic) oscillation, external main system clock input (EXCLK) HS (high-speed main) mode: 1 to 20 MHz ($VDD = 2.7$ to 5.5 V), HS (high-speed main) mode: 1 to 16 MHz ($VDD = 2.4$ to 5.5 V), LS (low-speed main) mode: 1 to 8 MHz ($VDD = 1.8$ to 5.5 V), LV (low-voltage main) mode: 1 to 4 MHz ($VDD = 1.6$ to 5.5 V) HS (high-speed main) mode: 1 to 32 MHz ($VDD = 2.7$ to 5.5 V),						
		LS (low-speed main) mode	e: 1 to 8 MHz (VDD = 1.8	to 5.5 V),				
Subsystem clock		LV (low-voltage main) mod	ue: 1 to 4 MHZ (VDD = 1.t	10 5.5 V)	XT1 (crystal) oscillation, external subsystem clock input (EXCLKS) 32.768 kHz			
Low-speed on-chi	p oscillator clock	15 kHz (TYP.): VDD = 1.6 t	o 5.5 V					
General-purpose	register	8 bits \times 32 registers (8 bits	$s \times 8$ registers $\times 4$ banks)					
Minimum instructi	on execution time	$0.03125\mu s$ (High-speed o	n-chip oscillator clock: fін	= 32 MHz operation)				
		$0.05 \ \mu s$ (High-speed syste	em clock: fmx = 20 MHz op	eration)				
			—		30.5 μs (Subsystem clock: fsuв = 32.768 kHz operation)			
Instruction set		 Data transfer (8/16 bits) Adder and subtractor/logical operation (8/16 bits) Multiplication (8 bits × 8 bits, 16 bits × 16 bits), Division (16 bits ÷ 16 bits, 32 bits ÷ 32 bits) Multiplication and Accumulation (16 bits × 16 bits + 32 bits) Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc. 						
I/O port	Total	26	28	32	36			
	CMOS I/O	21	22	26	28			
	CMOS input	3	3	3	5			
	CMOS output	—	_	—	—			
	N-ch open-drain I/O (6 V tolerance)	2	3	3	3			
Timer	16-bit timer	8 channels (TAU: 4 channels, Timer R	RJ: 1 channel, Timer RD: 2	channels, Timer RG: 1 ch	annel)			
	Watchdog timer	1 channel						
	Real-time clock (RTC)	1 channel						
	12-bit interval timer	1 channel						
	Timer output	Timer outputs: 13 channels PWM outputs: 9 channels						
	RTC output		_		1 • 1 Hz (subsystem clock: fsub = 32.768 kHz)			

(Note is listed on the next page.)



(R20UT2944).

 Note
 The flash library uses RAM in self-programming and rewriting of the data flash memory.

 The target products and start address of the RAM areas used by the flash library are shown below.

 R5F104xL (x = G, L, M, P): Start address F3F00H

 For the RAM areas used by the flash library, see Self RAM list of Flash Self-Programming Library for RL78 Family



Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, low Note 1	IOL1	Per pin for P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P130, P140 to P147				20.0 Note 2	mA
		Per pin for P60 to P63				15.0 Note 2	mA
		Total of P00 to P04, P40 to P47,	$4.0~V \leq EV_{DD0} \leq 5.5~V$			70.0	mA
		P102, P120, P130, P140 to P145 (When duty ≤ 70% ^{Note 3})	$2.7~V \leq EV_{DD0} < 4.0~V$			15.0	mA
			$1.8 \text{ V} \leq \text{EV}_{\text{DD0}} < 2.7 \text{ V}$			9.0	mA
			$1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 1.8 \text{ V}$			4.5	mA
		Total of P05, P06, P10 to P17,	$4.0~V \leq EV_{DD0} \leq 5.5~V$			80.0	mA
		P30, P31, P50 to P57,	$2.7~V \leq EV_{DD0} < 4.0~V$			35.0	mA
		P60 to P67, P70 to P77, P80 to P87, P100, P101, P110	$1.8 \text{ V} \leq \text{EV}_{\text{DD0}} < 2.7 \text{ V}$			20.0	mA
		P111, P146, P147 (When duty \leq 70% ^{Note 3})	1.6 V ≤ EVDD0 < 1.8 V			10.0	mA
		Total of all pins (When duty \leq 70% ^{Note 3})				150.0	mA
	IOL2	Per pin for P20 to P27, P150 to P156				0.4 Note 2	mA
		Total of all pins (When duty \leq 70% ^{Note 3})	$1.6 V \le VDD \le 5.5 V$			5.0	mA

(TA = -40 to +85°C, 1.6 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

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Note 1. Value of current at which the device operation is guaranteed even if the current flows from an output pin to the EVsso, EVss1, and Vss pins.

Note 2. Do not exceed the total current value.

Note 3. Specification under conditions where the duty factor \leq 70%.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

- Total output current of pins = (IoL \times 0.7)/(n \times 0.01)
- <Example> Where n = 80% and IoL = 10.0 mA
 - Total output current of pins = $(10.0 \times 0.7)/(80 \times 0.01) \approx 8.7$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor.

A current higher than the absolute maximum rating must not flow into one pin.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



Items	Symbol	Conditions	3	MIN.	TYP.	MAX.	Unit
Input voltage, high	Vih1	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P140 to P147	Normal input buffer	0.8 EVddo		EVddo	V
	Vih2	P01, P03, P04, P10, P14 to P17, P30, P43, P44, P50, P53 to P55,	TTL input buffer $4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$	2.2		EVDD0	V
		P80, P81, P142, P143	TTL input buffer $3.3 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V}$	2.0		EVDD0	V
			TTL input buffer $1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V}$	1.5		EVDD0	V
	Vінз	P20 to P27, P150 to P156	·	0.7 Vdd		Vdd	V
	VIH4	P60 to P63	0.7 EVDD0		6.0	V	
	Vih5	P121 to P124, P137, EXCLK, EX	CLKS, RESET	0.8 Vdd		Vdd	V
Input voltage, low	VIL1	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P140 to P147	Normal input buffer	0		0.2 EVDD0	V
	VIL2	P01, P03, P04, P10, P14 to P17, P30, P43, P44, P50, P53 to P55,	TTL input buffer $4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$	0		0.8	V
		P80, P81, P142, P143	TTL input buffer $3.3 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V}$	0		0.5	V
			TTL input buffer 1.6 V ≤ EVpp₀ < 3.3 V	0		0.32	V
	VIL3	P20 to P27, P150 to P156		0		0.3 Vdd	V
	VIL4	P60 to P63		0		0.3 EVDD0	V
	VIL5	P121 to P124, P137, EXCLK, EX	CLKS, RESET	0		0.2 Vdd	V

(TA = -40 to +85°C, 1.6 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

(3/5)

Caution The maximum value of VIH of pins P00, P02 to P04, P10, P11, P13 to P15, P17, P30, P43 to P45, P50 to P55, P71, P74, P80 to P82, and P142 to P144 is EVDD0, even in the N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



(TA = -40 to +8	5°C, 1.6	$\mathbf{V} \leq \mathbf{EV} \mathbf{DD}$	$\mathbf{D} = \mathbf{EV}\mathbf{D}\mathbf{D}1 \leq \mathbf{V}\mathbf{D}\mathbf{D} \leq \mathbf{C}$	5.5 V, Vss = I	EVsso	= EVSS1 = 0	V)			(2/2)
Parameter	Symbol		Conditions	HS (high-spee mode	d main)	LS (low-speed main) mode		LV (low-voltage mode	e main)	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SSI00 setup time	tssik	DAPmn = 0	$2.7~V \leq EV_{DD0} \leq 5.5~V$	120		120		120		ns
			$1.8 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$	200		200		200		ns
			$1.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$	400		400		400		ns
			$1.6 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$	—		400		400		ns
		DAPmn = 1	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$	1/fмск + 120		1/fмск + 120		1/fмск + 120		ns
			$1.8 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$	1/fмск + 200		1/fмск + 200		1/fмск + 200		ns
			$1.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$	1/fмск + 400		1/fмск + 400		1/fмск + 400		ns
			$1.6 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$	—		1/fмск + 400		1/fмск + 400		ns
SSI00 hold time	tĸssi	DAPmn = 0	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$	1/fмск + 120		1/fмск + 120		1/fмск + 120		ns
			$1.8 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$	1/fмск + 200		1/fмск + 200		1/fмск + 200		ns
			$1.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$	1/fмск + 400		1/fмск + 400		1/fмск + 400		ns
			$1.6 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$	—		1/fмск + 400		1/fмск + 400		ns
		DAPmn = 1	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$	120		120		120		ns
			$1.8 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$	200		200		200		ns
			$1.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$	400		400		400		ns
			$1.6 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$	_		400		400		ns

(4) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input) (TA = -40 to +85°C, 1.6 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V)

Caution Select the normal input buffer for the SIp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remark p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM number (g = 3, 5)

CSI mode connection diagram (during communication at same potential)



CSI mode connection diagram (during communication at same potential) (Slave Transmission of slave select input function (CSI00))



Remark 1. p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31) **Remark 2.** m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13)



UART mode connection diagram (during communication at different potential)



UART mode bit width (during communication at different potential) (reference)





Remark 1. $Rb[\Omega]$: Communication line (TxDq) pull-up resistance,

Cb[F]: Communication line (TxDq) load capacitance, Vb[V]: Communication line voltage

Remark 2. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 5, 14)

Remark 3. fMCK: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

Remark 4. UART2 cannot communicate at different potential when bit 1 (PIOR01) of peripheral I/O redirection register 0 (PIOR0) is 1.



3. ELECTRICAL SPECIFICATIONS (G: INDUSTRIAL APPLICATIONS TA = -40 to +105°C)

This chapter describes the following electrical specifications. Target products G: Industrial applications $T_A = -40$ to $+105^{\circ}C$ R5F104xxGxx

- Caution 1. The RL78 microcontrollers have an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.
- Caution 2. With products not provided with an EVDD0, EVDD1, EVSS0, or EVSS1 pin, replace EVDD0 and EVDD1 with VDD, or replace EVSS0 and EVSS1 with VSS.
- Caution 3. The pins mounted depend on the product. Refer to 2.1 Port Functions to 2.2.1 Functions for each product in the RL78/G14 User's Manual.
- Caution 4. Please contact Renesas Electronics sales office for derating of operation under TA = +85 to +105°C. Derating is the systematic reduction of load for the sake of improved reliability.
- Remark When RL78/G14 is used in the range of T_A = -40 to +85°C, see 2. ELECTRICAL SPECIFICATIONS (T_A = -40 to +85°C).



3.2 Oscillator Characteristics

3.2.1 X1, XT1 characteristics

$(TA = -40 \text{ to } +105^{\circ}C, 2.4 \text{ V} \le \text{VDD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Resonator	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock oscillation frequency (fx) Note	Ceramic resonator/	$2.7~V \leq V \text{DD} \leq 5.5~V$	1.0		20.0	MHz
	crystal resonator	$2.4 \text{ V} \le \text{V}_{\text{DD}} \le 2.7 \text{ V}$	1.0		16.0	
XT1 clock oscillation frequency (fxT) Note	Crystal resonator		32	32.768	35	kHz

Note Indicates only permissible oscillator frequency ranges. Refer to AC Characteristics for instruction execution time. Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.

Caution Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.

Remark When using the X1 oscillator and XT1 oscillator, refer to 5.4 System Clock Oscillator in the RL78/G14 User's Manual.

3.2.2 On-chip oscillator characteristics

(TA = -40 to +105°C, 2.4 V \leq VDD \leq 5.5 V, Vss = 0 V)

Oscillators	Parameters	Co	onditions	MIN.	TYP.	MAX.	Unit
High-speed on-chip oscillator clock frequency Notes 1, 2	fін					32	MHz
High-speed on-chip oscillator clock frequency		-20 to +85°C	$2.4~V \leq V \text{DD} \leq 5.5~V$	-1.0		+1.0	%
accuracy		-40 to -20°C	$2.4~V \leq V \text{DD} \leq 5.5~V$	-1.5		+1.5	%
		+85 to +105°C	$2.4~V \leq V \text{DD} \leq 5.5~V$	-2.0		+2.0	%
Low-speed on-chip oscillator clock frequency	fı∟				15		kHz
Low-speed on-chip oscillator clock frequency accuracy				-15		+15	%

Note 1. High-speed on-chip oscillator frequency is selected with bits 0 to 4 of the option byte (000C2H) and bits 0 to 2 of the HOCODIV register.

Note 2. This only indicates the oscillator characteristics. Refer to AC Characteristics for instruction execution time.



Items	Symbol	Conditi	ons		MIN.	TYP.	MAX.	Unit
Input leakage cur- rent, high	ILIH1	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P140 to P147	VI = EVDDO				1	μA
	Ilih2	P20 to P27, P137, P150 to P156, RESET	VI = VDD				1	μA
	Ілнз	P121 to P124 (X1, X2, EXCLK, XT1, XT2, EXCLKS)	VI = VDD	In input port or external clock input			1	μA
				In resonator con- nection			10	μA
Input leakage current, low On-chip pull-up resistance	ILIL1	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P140 to P147	VI = EVsso			-1	μΑ	
	ILIL2	P20 to P27, P137, P150 to P156, RESET	VI = VSS				-1	μA
	Ilil3	P121 to P124 (X1, X2, EXCLK, XT1, XT2, EXCLKS)	VI = VSS	In input port or external clock input			-1	μΑ
				In resonator con- nection			-10	μA
On-chip pull-up resistance	Ru	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P140 to P147	Vi = EVsso, In input port		10	20	100	kΩ

(TA = -40 to +105°C, 2.4 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

(5/5)

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



3.3.2 Supply current characteristics

(1) Flash ROM: 16 to 64 KB of 30- to 64-pin products

(TA = -40 to +105°C, 2.4 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVsso = 0 V)

Parameter	Symbol		Conditions						MAX.	Unit
Supply	IDD1	Operat-	HS (high-speed main)	fносо = 64 MHz,	Basic	VDD = 5.0 V		2.4		mA
current		ing mode	mode Note 5	fiH = 32 MHz Note 3	operation	VDD = 3.0 V		2.4		
Note 1				fносо = 32 MHz,	Basic	VDD = 5.0 V		2.1		
				fiH = 32 MHz Note 3	operation	VDD = 3.0 V		2.1		
			HS (high-speed main)	fносо = 64 MHz,	Normal	VDD = 5.0 V		5.1	9.3	mA
			mode Note 5	fiH = 32 MHz Note 3	operation	VDD = 3.0 V		5.1	9.3	
				fносо = 32 MHz,	Normal	VDD = 5.0 V		4.8	8.7	
				fiH = 32 MHz Note 3	operation	VDD = 3.0 V		4.8	8.7	
				fносо = 48 MHz,	Normal	VDD = 5.0 V		4.0	7.3	
				fiH = 24 MHz Note 3	operation	VDD = 3.0 V		4.0	7.3	
				fносо = 24 MHz,	Normal	VDD = 5.0 V		3.8	6.7	
				fiH = 24 MHz Note 3	operation	VDD = 3.0 V		3.8	6.7	
				fносо = 16 MHz, Normal	Normal	VDD = 5.0 V		2.8	4.9	
				fiH = 16 MHz Note 3 f _{MX} = 20 MHz Note 2, V _{DD} = 5.0 V	operation	VDD = 3.0 V		2.8	4.9	
			HS (high-speed main) mode Note 5		Normal	Square wave input		3.3	5.7	mA
					operation	Resonator connection		3.4	5.8	
			f _{MX} = 20 MHz ^{Note 2} ,	Normal	Square wave input		3.3	5.7		
			VDD = 3.0 V	operation	Resonator connection		3.4	5.8		
				fmx = 10 MHz Note 2,	Normal	Square wave input		2.0	3.4	
				V _{DD} = 5.0 V	operation	Resonator connection		2.1	3.5	
				f _{MX} = 10 MHz ^{Note 2} , V _{DD} = 3.0 V	Normal	Square wave input		2.0	3.4	
					operation	Resonator connection		2.1	3.5	
			Subsystem clock	fsub = 32.768 kHz Note 4	Normal	Square wave input		4.7	6.1	μΑ
			operation	TA = -40°C	operation	Resonator connection		4.7	6.1	
				fsue = 32.768 kHz Note 4	Normal	Square wave input		4.7	6.1	
				TA = +25°C	operation	Resonator connection		4.7	6.1	
				fsue = 32.768 kHz Note 4	Normal	Square wave input		4.8	6.7	
				TA = +50°C	operation	Resonator connection		4.8	6.7	
				fsub = 32.768 kHz Note 4	Normal	Square wave input		4.8	7.5	
		T	TA = +70°C	operation	Resonator connection		4.8	7.5		
				fsue = 32.768 kHz Note 4	Normal	Square wave input		5.4	8.9	
		TA	TA = +85°C	operation	Resonator connection		5.4	8.9		
			fs	fsub = 32.768 kHz Note 4	Normal	Square wave input		7.2	21.0	
			TA = +105°C	operation	Resonator connection		7.3	21.1		

(Notes and Remarks are listed on the next page.)



- Note 1. Total current flowing into VDD and EVDD0, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDD0 or Vss, EVss0. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
- Note 2. When high-speed on-chip oscillator and subsystem clock are stopped.
- **Note 3.** When high-speed system clock and subsystem clock are stopped.
- **Note 4.** When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
- **Note 5.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below. HS (high-speed main) mode: $2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}_{@}1 \text{ MHz}$ to 32 MHz
 - 2.4 V \leq VDD \leq 5.5 V@1 MHz to 16 MHz
- Remark 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
- Remark 2. fHoco: High-speed on-chip oscillator clock frequency (64 MHz max.)
- Remark 3. fin: High-speed on-chip oscillator clock frequency (32 MHz max.)
- **Remark 4.** fsuB: Subsystem clock frequency (XT1 clock oscillation frequency)
- Remark 5. Except subsystem clock operation, temperature condition of the TYP. value is TA = 25°C



(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output)

(TA = -40 to +105°C, 2.4 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)				(2/3)	
Parameter	Symbol	Conditions	HS (high-speed main) mode		Unit
			MIN.	MAX.	
SIp setup time (to SCKp↑) ^{Note}	tsiк1		162		ns
		$\begin{array}{l} 2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 30 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	354		ns
		$\begin{array}{l} 2.4 \; V \leq EV_{DD0} < 3.3 \; V, \\ 1.6 \; V \leq V_b \leq 2.0 \; V, \\ C_b = 30 \; pF, \; R_b = 5.5 \; k\Omega \end{array}$	958		ns
SIp hold time (from SCKp↑) ^{Note}	tksi1		38		ns
		$\begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 30 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	38		ns
		$\label{eq:2.4} \begin{array}{l} 2.4 \ V \leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V, \\ C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega \end{array}$	38		ns
Delay time from SCKp↓ to SOp output ^{Note}	tkso1			200	ns
		$\begin{array}{l} 2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 30 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$		390	ns
		$\begin{array}{l} 2.4 \; V \leq EV_{DD0} < 3.3 \; V, \\ 1.6 \; V \leq V_b \leq 2.0 \; V, \\ C_b = 30 \; pF, \; R_b = 5.5 \; k\Omega \end{array}$		966	ns

Note When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

(Remarks are listed on the page after the next page.)



Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (for the 30- to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I²C mode)

(TA = -40 to +105°C, 2	$2.4 V \leq EVDD0 = EVDD^{2}$	$1 \leq VDD \leq 5.5 V, VSS$	= EVss0 $=$ EVss1 $=$ 0 V)
(

(1/2)

Parameter	Symbol	Conditions	HS (high-spe	ed main) mode	Unit
			MIN.	MAX.	
SCLr clock frequency	fsc∟			400 Note 1	kHz
		$\begin{array}{l} 2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$		400 Note 1	kHz
		$\begin{array}{l} 4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ 2.7 \; V \leq V_{b} \leq 4.0 \; V, \\ C_{b} = 100 \; pF, \; R_{b} = 2.8 \; k\Omega \end{array}$		100 Note 1	kHz
		$\begin{array}{l} 2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 100 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$		100 Note 1	kHz
		$\label{eq:2.4} \begin{array}{l} 2.4 \; V \leq EV_{DD0} < 3.3 \; V, \\ 1.6 \; V \leq V_b \leq 2.0 \; V, \\ C_b = 100 \; pF, \; R_b = 5.5 \; k\Omega \end{array}$		100 Note 1	kHz
Hold time when SCLr = "L"	t.ow		1200		ns
		$\begin{array}{l} 2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	1200		ns
			4600		ns
		$\begin{array}{l} 2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 100 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	4600		ns
		$\begin{array}{l} 2.4 \; V \leq EV_{DD0} < 3.3 \; V, \\ 1.6 \; V \leq V_b \leq 2.0 \; V, \\ C_b = 100 \; pF, \; R_b = 5.5 \; k\Omega \end{array}$	4650		ns
Hold time when SCLr = "H"	tнigн		620		ns
		$\begin{array}{l} 2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	500		ns
			2700		ns
		$\label{eq:2.7} \begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 100 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	2400		ns
		$\label{eq:2.4} \begin{array}{l} 2.4 \; V \leq EV_{DD0} < 3.3 \; V, \\ 1.6 \; V \leq V_b \leq 2.0 \; V, \\ C_b = 100 \; pF, \; R_b = 5.5 \; k\Omega \end{array}$	1830		ns



(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I²C mode)

1	[/ – -40 to +105°C 24 V < EV_00 – EV_01 < V00 < 55 V V99 – EV990 – EV991 − 0	n vn
1	$A = -40 \ 10 + 103 \ C, 2.4 \ V \ge EVDD0 = EVDD1 \ge VDD \ge 3.5 \ V, V33 = EV330 = EV331 = 0$, v)

(2/2)

Parameter	Symbol	Conditions	HS (high-speed main) mode		Unit
			MIN.	MAX.	
Data setup time (reception)	tsu:dat		1/f _{MCK} + 340 Note 2		ns
		$\begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 50 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	1/fмск + 340 Note 2		ns
			1/fmck + 760 Note 2		ns
		$\label{eq:2.7} \begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 100 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	1/fмск + 760 Note 2		ns
		$\label{eq:2.4} \begin{array}{l} 2.4 \ V \leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V, \\ C_b = 100 \ pF, \ R_b = 5.5 \ k\Omega \end{array}$	1/fмск + 570 Note 2		ns
Data hold time (transmission)	thd:dat		0	770	ns
		$\begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 50 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	0	770	ns
			0	1420	ns
		$\label{eq:2.7} \begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 100 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	0	1420	ns
		$\begin{array}{l} 2.4 \ V \leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V, \\ C_b = 100 \ pF, \ R_b = 5.5 \ k\Omega \end{array}$	0	1215	ns

Note 1. The value must also be equal to or less than fMCK/4.

Note 2. Set the fMCK value to keep the hold time of SCLr = "L" and SCLr = "H".

Caution Select the TTL input buffer and the N-ch open drain output (VDD tolerance (for the 30- to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the SDAr pin and the N-ch open drain output (VDD tolerance (for the 30- to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(**Remarks** are listed on the next page.)



4.3 36-pin products

R5F104CAALA, R5F104CCALA, R5F104CDALA, R5F104CEALA, R5F104CFALA, R5F104CGALA R5F104CAGLA, R5F104CCGLA, R5F104CDGLA, R5F104CEGLA, R5F104CFGLA, R5F104CGGLA



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R5F104GKAFB, R5F104GLAFB R5F104GKGFB, R5F104GLGFB





R5F104LCAFB, R5F104LDAFB, R5F104LEAFB, R5F104LFAFB, R5F104LGAFB, R5F104LHAFB, R5F104LJAFB

R5F104LCDFB, R5F104LDDFB, R5F104LEDFB, R5F104LFDFB, R5F104LGDFB, R5F104LHDFB, R5F104LJDFB

R5F104LCGFB, R5F104LDGFB, R5F104LEGFB, R5F104LFGFB, R5F104LGGFB, R5F104LHGFB, R5F104LJGFB

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LFQFP64-10x10-0.50	PLQP0064KF-A	P64GB-50-UEU-2	0.35



Each lead centerline is located within 0.08 mm of its true position at maximum material condition.

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R5F104LCAFP, R5F104LDAFP, R5F104LEAFP, R5F104LFAFP, R5F104LGAFP, R5F104LHAFP, R5F104LJAFP R5F104LCDFP, R5F104LDDFP, R5F104LEDFP, R5F104LFDFP, R5F104LGDFP, R5F104LHDFP, R5F104LJDFP R5F104LCGFP, R5F104LDGFP, R5F104LEGFP, R5F104LFGFP, R5F104LGGFP, R5F104LHGFP, R5F104LJGFP

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP64-14x14-0.80	PLQP0064GA-A	P64GC-80-GBW-1	0.7



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